



NETSOL Product list

Synchronous SRAM

Asynchronous Fast SRAM

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NETSOL Co., LTD
www.netsol.co.kr

High Quality & High Performance Memory Provider for Network Solution

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Standard Synchronous SRAM

: SPB and FT

Density	Org.	Part Number	Operation Mode	Vdd (V)	Speed (MHz)	Package	Availability
4Mb	128Kx36	S7A403630M	SPB	2.5/3.3	250MHz	100TQFP	Now
		S7B403635M	FT	2.5/3.3	250MHz	100TQFP	Now
	256Kx18	S7A401830M	SPB	2.5/3.3	250MHz	100TQFP	Now
		S7B401835M	FT	2.5/3.3	250MHz	100TQFP	Now
9Mb	256Kx36	S7A803630M	SPB	2.5/3.3	250MHz	100TQFP	Now
		S7B803635M	FT	2.5/3.3	250MHz	100TQFP	Now
	512Kx18	S7A801830M	SPB	2.5/3.3	250MHz	100TQFP	Now
		S7B801835M	FT	2.5/3.3	250MHz	100TQFP	Now
18Mb	512Kx36	S7A163630M	SPB	2.5/3.3	250MHz	100TQFP	Now
		S7B163635M	FT	2.5/3.3	250MHz	100TQFP	Now
	1Mx18	S7A161830M	SPB	2.5/3.3	250MHz	100TQFP	Now
		S7B161835M	FT	2.5/3.3	250MHz	100TQFP	Now
36Mb	1Mx36	S7A323630M	SPB	2.5/3.3	250MHz	100TQFP	Now
		S7B323635M	FT	2.5/3.3	250MHz	100TQFP	Now
	2Mx18	S7A321830M	SPB	2.5/3.3	250MHz	100TQFP	Now
		S7B321835M	FT	2.5/3.3	250MHz	100TQFP	Now

Notes

1. All of SPB products and FT are based on RoHS6, lead free 100TQFP package.
2. SPB: Synchronous Pipelined Burst, FT: Flow-Through
3. Both commercial temperature range and industrial are available.
4. Single bin policy by 250Mhz for SPB and by 6.5ns for FT.
Faster than 250Mhz are possible upon request.
5. Non-parity such as 32-bits is possible upon request.
6. All of SPB is based on 2E1D, and 2E2D could be considered upon request.

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Standard Synchronous SRAM

: NTSRAM (NT-SPB & NT-FT)

Density	Org.	Part Number	Operation Mode	Vdd (V)	Speed (MHz)	Package	Availability
4Mb	128Kx36	S7N403631M	NT-SPB	2.5/3.3	250MHz	100TQFP	Now
		S7M403635M	NT-FT	2.5/3.3	250MHz	100TQFP	Now
	256Kx18	S7N401831M	NT-SPB	2.5/3.3	250MHz	100TQFP	Now
		S7M401835M	NT-FT	2.5/3.3	250MHz	100TQFP	Now
9Mb	256Kx36	S7N803631M	NT-SPB	2.5/3.3	250MHz	100TQFP	Now
		S7M803635M	NT-FT	2.5/3.3	250MHz	100TQFP	Now
	512Kx18	S7N801831M	NT-SPB	2.5/3.3	250MHz	100TQFP	Now
		S7M801835M	NT-FT	2.5/3.3	250MHz	100TQFP	Now
18Mb	512Kx36	S7N163631M	NT-SPB	2.5/3.3	250MHz	100TQFP 165FBGA	Now
		S7M163635M	NT-FT	2.5/3.3	250MHz	100TQFP 165FBGA	Now
	1Mx18	S7N161831M	NT-SPB	2.5/3.3	250MHz	100TQFP	Now
		S7M161835M	NT-FT	2.5/3.3	250MHz	100TQFP	Now
36Mb	1Mx36	S7N323631M	NT-SPB	2.5/3.3	250MHz	100TQFP 165FBGA	Now
		S7M323635M	NT-FT	2.5/3.3	250MHz	100TQFP 165FBGA	Now
	2Mx18	S7N321831M	NT-SPB	2.5/3.3	250MHz	100TQFP	Now
		S7M321835M	NT-FT	2.5/3.3	250MHz	100TQFP	Now
72Mb	1Mx36	S7N643631M	NT-SPB	2.5/3.3	250MHz	100TQFP	Early Q3'13
		S7M643635M	NT-FT	2.5/3.3	250MHz	100TQFP	Early Q3'13
	2Mx18	S7N641831M	NT-SPB	2.5/3.3	250MHz	100TQFP	Early Q3'13
		S7M641835M	NT-FT	2.5/3.3	250MHz	100TQFP	Early Q3'13

Notes

1. All of NTSRAM products are based on RoHS6.
All NTSRAM is based on 100TQFP including 165FBGA for NT-SPB.
2. NTSRAM: Non-Turnaround Static Random Access Memory
3. Both commercial temperature range and industrial are available.
4. Single bin policy by 250Mhz for NT-SPB and by 6.5ns for NT-FT.
Faster than 250Mhz are possible upon request.
5. Non-parity such as 32-bits is possible upon request.

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Quadruple and DDR Synchronous SRAM : **Quadruple-I**

Density	Org.	Part Number	Burst Length	Vdd (V)	VddQ (V)	Speed (MHz)	Package	Availability
18Mb	512Kx36	S7Q163662M	2	1.8/2.5	1.5/1.8	167MHz	165FBGA	Now
	1Mx18	S7Q161862M						
	512Kx36	S7Q163664M	4	1.8/2.5	1.5/1.8	167MHz	165FBGA	Now
	1Mx18	S7Q161864M						

Notes

1. All of RoHS5 or leaded type is recommended to convert it into RoHS6 or lead free.
2. Both commercial temperature range and industrial are available.

High Quality & High Performance Memory Provider for **Network Solution**

Quadruple and DDR Synchronous SRAM

: Quadruple-II

Density	Org.	Part Number	Burst Length	Vdd (V)	VddQ (V)	Speed (MHz)	Package	Availability		
18Mb	512Kx36	S7R163682M	2	1.8	1.5/1.8	333	165FBGA	Now		
	1Mx18	S7R161882M				300				
	2Mx9	S7R160982M				250				
	512Kx36	S7R163684M	4			333			165FBGA	Now
	1Mx18	S7R161884M				300				
	2Mx9	S7R160984M				250				
36Mb	1Mx36	S7R323682M	2	1.8	1.5/1.8	350	165FBGA	Now		
	2Mx18	S7R321882M				333				
	4Mx9	S7R320982M				300				
	1Mx36	S7R323684M	4			333			165FBGA	Now
	2Mx18	S7R321884M				300				
	4Mx9	S7R320984M				250				
72Mb	2Mx36	S7R643682M	2	1.8	1.5/1.8	333	165FBGA	Early Q3'13		
	4Mx18	S7R641882M				300				
	8Mx9	S7R640982M				250				
	2Mx36	S7R643684M	4			333			165FBGA	Early Q3'13
	4Mx18	S7R641884M				300				
	8Mx9	S7R640984M				250				

Notes

1. All of RoHS5 or leaded type is recommended to convert it into RoHS6 or lead free.
2. Both commercial temperature range and industrial are available.
3. Lower bins such as 200Mhz and 167Mhz are recommended to 250Mhz.

High Quality & High Performance Memory Provider for Network Solution

Quadruple and DDR Synchronous SRAM : **DDR-II, Common I/O**

Density	Org.	Part Number	Burst Length	Vdd (V)	VddQ (V)	Speed (MHz)	Package	Availability
18Mb	512Kx36	S7I163682M	2	1.8	1.5/1.8	333	165FBGA	Now
	1Mx18	S7I161882M				250		
	512Kx36	S7I163684M	4	1.8	1.5/1.8	333	165FBGA	Now
	1Mx18	S7I161884M				250		
36Mb	1Mx36	S7I323682M	2	1.8	1.5/1.8	333	165FBGA	Now
	2Mx18	S7I321882M				250		
	1Mx36	S7I323684M	4	1.8	1.5/1.8	333	165FBGA	Now
	2Mx18	S7I321884M				250		
72Mb	2Mx36	S7I643682M	2	1.8	1.5/1.8	333	165FBGA	Early Q3'13
	4Mx18	S7I641882M				250		
	2Mx36	S7I643684M	4	1.8	1.5/1.8	333	165FBGA	Early Q3'13
	4Mx18	S7I641884M				250		

Notes

1. All of RoHS5 or leaded type is recommended to convert it into RoHS6 or lead free.
2. Both commercial temperature range and industrial are available.
3. Lower bins such as 200Mhz and 167Mhz are recommended to 250Mhz.

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Quadruple and DDR Synchronous SRAM : **DDR-II, Separate I/O**

Density	Org.	Part Number	Burst Length	Vdd (V)	VddQ (V)	Speed (MHz)	Package	Availability
18Mb	512Kx36	S7J163682M	2	1.8	1.5/1.8	333, 300, 250	165FBGA	Now
	1Mx18	S7J161882M						
	2Mx9	S7J160984M						
36Mb	512Kx36	S7J323682M	2	1.8	1.5/1.8	333, 300, 250	165FBGA	Now
	1Mx18	S7J321882M						
	2Mx9	S7J320984M						
72Mb	512Kx36	S7J643682M	2	1.8	1.5/1.8	333, 300, 250	165FBGA	Early Q3'13
	1Mx18	S7J641882M						
	2Mx9	S7J640984M						

Notes

1. All of RoHS5 or leaded type is recommended to convert it into RoHS6 or lead free.
2. Both commercial temperature range and industrial are available.
3. Lower bins such as 200Mhz and 167Mhz are recommended to 250Mhz.

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Quadruple and DDR Synchronous SRAM : Quadruple-II+, 2.0 CL, without ODT

■ 2.0 Clock Latency, without ODT(On Die Termination)

Density	Org.	Part Number	Burst Length	Vdd (V)	VddQ (V)	Speed (MHz)	Package	Availability
18Mb	512Kx36	S7S1636T2M	2	1.8	1.5/1.8	400 333	165FBGA	U/C
	1Mx18	S7S1618T2M						
	2Mx9	S7S1609T2M						
	512Kx36	S7S1636T4M	4	1.8	1.5/1.8	450 400	165FBGA	Now
	1Mx18	S7S1618T4M						
	2Mx9	S7S1609T4M						
36Mb	1Mx36	S7S3236T2M	2	1.8	1.5/1.8	400 333	165FBGA	U/C
	2Mx18	S7S3218T2M						
	4Mx9	S7S3209T2M						
	1Mx36	S7S3236T4M	4	1.8	1.5/1.8	450 400	165FBGA	Now
	2Mx18	S7S3218T4M						
	4Mx9	S7S3209T4M						
72Mb	2Mx36	S7S6436T2M	2	1.8	1.5/1.8	400 333	165FBGA	U/C
	4Mx18	S7S6418T2M						
	8Mx9	S7S6409T2M						
	2Mx36	S7S6436T4M	4	1.8	1.5/1.8	450 400	165FBGA	Early Q3'13
	4Mx18	S7S6418T4M						
	8Mx9	S7S6409T4M						

Notes

1. All of RoHS5 or leaded type is recommended to convert it into RoHS6 or lead free.
2. Both commercial temperature range and industrial are available.
3. U/C, under consideration, stands for products available upon request.

High Quality & High Performance Memory Provider for Network Solution

Quadruple and DDR Synchronous SRAM : **Quadruple-II+, 2.0 CL, with ODT**

■ 2.0 Clock Latency, with ODT(On Die Termination)

Density	Org.	Part Number	Burst Length	Vdd (V)	VddQ (V)	Speed (MHz)	Package	Availability
18Mb	512Kx36	S7T1636T2M	2	1.8	1.5/1.8	400 333	165FBGA	U/C
	1Mx18	S7T1618T2M						
	2Mx9	S7T1609T2M						
	512Kx36	S7T1636T4M	4	1.8	1.5/1.8	450 400	165FBGA	Now
	1Mx18	S7T1618T4M						
	2Mx9	S7T1609T4M						
36Mb	1Mx36	S7T3236T2M	2	1.8	1.5/1.8	400 333	165FBGA	U/C
	2Mx18	S7T3218T2M						
	4Mx9	S7T3209T2M						
	1Mx36	S7T3236T4M	4	1.8	1.5/1.8	450 400	165FBGA	Now
	2Mx18	S7T3218T4M						
	4Mx9	S7T3209T4M						
72Mb	2Mx36	S7T6436T2M	2	1.8	1.5/1.8	400 333	165FBGA	U/C
	4Mx18	S7T6418T2M						
	8Mx9	S7T6409T2M						
	2Mx36	S7T6436T4M	4	1.8	1.5/1.8	450 400	165FBGA	Early Q3'13
	4Mx18	S7T6418T4M						
	8Mx9	S7T6409T4M						

Notes

1. All of RoHS5 or leaded type is recommended to convert it into RoHS6 or lead free.
2. Both commercial temperature range and industrial are available.
3. U/C, under consideration, stands for products available upon request.

High Quality & High Performance Memory Provider for **Network Solution**

Quadruple and DDR Synchronous SRAM : Quadruple-II+, 2.5 CL, without ODT

■ 2.5 Clock Latency, without ODT(On Die Termination)

Density	Org.	Part Number	Burst Length	Vdd (V)	VddQ (V)	Speed (MHz)	Package	Availability
18Mb	512Kx36	S7S1636U2M	2	1.8	1.5/1.8	450 400	165FBGA	U/C
	1Mx18	S7S1618U2M						
	2Mx9	S7S1609U2M						
	512Kx36	S7S1636U4M	4	1.8	1.5/1.8	550 500 450	165FBGA	Now
	1Mx18	S7S1618U4M						
	2Mx9	S7S1609U4M						
36Mb	1Mx36	S7S3236U2M	2	1.8	1.5/1.8	450 400	165FBGA	Now
	2Mx18	S7S3218U2M						
	4Mx9	S7S3209U2M						
	1Mx36	S7S3236U4M	4	1.8	1.5/1.8	550 500 450	165FBGA	Now
	2Mx18	S7S3218U4M						
	4Mx9	S7S3209U4M						
72Mb	2Mx36	S7S6436U2M	2	1.8	1.5/1.8	450 400	165FBGA	Early Q3'13
	4Mx18	S7S6418U2M						
	8Mx9	S7S6409U2M						
	2Mx36	S7S6436U4M	4	1.8	1.5/1.8	550 500 450	165FBGA	Early Q3'13
	4Mx18	S7S6418U4M						
	8Mx9	S7S6409U4M						

Notes

1. All of RoHS5 or leaded type is recommended to convert it into RoHS6 or lead free.
2. Both commercial temperature range and industrial are available.
3. U/C, under consideration, stands for products available upon request.

High Quality & High Performance Memory Provider for Network Solution

Quadruple and DDR Synchronous SRAM : Quadruple-II+, 2.5 CL, with ODT

■ 2.5 Clock Latency, with ODT(On Die Termination)

Density	Org.	Part Number	Burst Length	Vdd (V)	VddQ (V)	Speed (MHz)	Package	Availability
18Mb	512Kx36	S7T1636U2M	2	1.8	1.5/1.8	500 450	165FBGA	U/C
	1Mx18	S7T1618U2M						
	2Mx9	S7T1609U2M						
	512Kx36	S7T1636U4M	4	1.8	1.5/1.8	550 500 450	165FBGA	Now
	1Mx18	S7T1618U4M						
	2Mx9	S7T1609U4M						
36Mb	1Mx36	S7T3236U2M	2	1.8	1.5/1.8	500 450	165FBGA	U/C
	2Mx18	S7T3218U2M						
	4Mx9	S7T3209U2M						
	1Mx36	S7T3236U4M	4	1.8	1.5/1.8	550 500 450	165FBGA	Now
	2Mx18	S7T3218U4M						
	4Mx9	S7T3209U4M						
72Mb	2Mx36	S7T6436U2M	2	1.8	1.5/1.8	500 450	165FBGA	Early Q3'13
	4Mx18	S7T6418U2M						
	8Mx9	S7T6409U2M						
	2Mx36	S7T6436U4M	4	1.8	1.5/1.8	550 500 450	165FBGA	Early Q3'13
	4Mx18	S7T6418U4M						
	8Mx9	S7T6409U4M						

Notes

1. All of RoHS5 or leaded type is recommended to convert it into RoHS6 or lead free.
2. Both commercial temperature range and industrial are available.
3. U/C, under consideration, stands for products available upon request.

High Quality & High Performance Memory Provider for Network Solution

Quadruple and DDR Synchronous SRAM

: DDR-II+, Common I/O, 2.0CL

■ 2.0 Clock Latency, without ODT(On Die Termination)

Density	Org.	Part Number	Burst Length	Vdd (V)	VddQ (V)	Speed (MHz)	Package	Avail-Ability
18Mb	512Kx36	S7K1636T2M	2	1.8	1.5/1.8	450	165FBGA	Now
	1Mx18	S7K1618T2M				400		
36Mb	1Mx36	S7K3236T2M	2	1.8	1.5/1.8	450	165FBGA	Now
	2Mx18	S7K3218T2M				400		
72Mb	2Mx36	S7K6436T2M	2	1.8	1.5/1.8	450	165FBGA	Early Q3'13
	4Mx18	S7K6418T2M				400		

■ 2.0 Clock Latency, with ODT(On Die Termination)

Density	Org.	Part Number	Burst Length	Vdd (V)	VddQ (V)	Speed (MHz)	Package	Avail-ability
18Mb	512Kx36	S7L1636T2M	2	1.8	1.5/1.8	450	165FBGA	Now
	1Mx18	S7L1618T2M				400		
36Mb	1Mx36	S7L3236T2M	2	1.8	1.5/1.8	450	165FBGA	Now
	2Mx18	S7L3218T2M				400		
72Mb	2Mx36	S7L6436T2M	2	1.8	1.5/1.8	450	165FBGA	Early Q3'13
	4Mx18	S7L6418T2M				400		

Notes

1. All of RoHS5 or leaded type is recommended to convert it into RoHS6 or lead free.
2. Both commercial temperature range and industrial are available.

High Quality & High Performance Memory Provider for Network Solution

Quadruple and DDR Synchronous SRAM

: DDR-II+, Common I/O, 2.5CL

■ 2.5 Clock Latency, without ODT(On Die Termination)

Density	Org.	Part Number	Burst Length	Vdd (V)	VddQ (V)	Speed (MHz)	Package	Availability
18Mb	512Kx36	S7K1636U2M	2	1.8	1.5/1.8	550	165FBGA	Now
	1Mx18	S7K1618U2M				450		
36Mb	1Mx36	S7K3236U2M	2	1.8	1.5/1.8	550	165FBGA	Now
	2Mx18	S7K3218U2M				450		
72Mb	2Mx36	S7K6436U2M	2	1.8	1.5/1.8	550	165FBGA	Early Q3'13
	4Mx18	S7K6418U2M				450		

■ 2.5 Clock Latency, with ODT(On Die Termination)

Density	Org.	Part Number	Burst Length	Vdd (V)	VddQ (V)	Speed (MHz)	Package	Availability
18Mb	512Kx36	S7L1636U2M	2	1.8	1.5/1.8	550	165FBGA	Now
	1Mx18	S7L1618U2M				450		
36Mb	1Mx36	S7L3236U2M	2	1.8	1.5/1.8	550	165FBGA	Now
	2Mx18	S7L3218U2M				450		
72Mb	2Mx36	S7L6436U2M	2	1.8	1.5/1.8	550	165FBGA	Early Q3'13
	4Mx18	S7L6418U2M				450		

Notes

1. All of RoHS5 or leaded type is recommended to convert it into RoHS6 or lead free.
2. Both commercial temperature range and industrial are available.

High Quality & High Performance Memory Provider for Network Solution

Asynchronous Fast SRAM

■ Packaged Product

Density	Org.	Part Number	Vdd (V)	Speed -tAA(ns)	Package	Availability
4Mb	256Kx16	S6R4016V1M	3.3	10	44TSOP2	Now
		S6R4016C1M	5.0	10	44TSOP2	Now
	512Kx8	S6R4008V1M	3.3	10	44TSOP2	Now
		S6R4008C1M	5.0	10	44TSOP2	Now
8Mb	512Kx16	S6R8016V1M	3.3	10	44TSOP2	Now
		S6R8016C1M	5.0	10	44TSOP2	Now
	1Mx8	S6R8008V1M	3.3	10	44TSOP2	Now
		S6R8008C1M	5.0	10	44TSOP2	Now
16Mb	1Mx16	S6R1616V1M	3.3	10	48TSOP1	Now
					54TSOP2	U/C
		S6R1616C1M	5.0	10	48TSOP1	Now
	2Mx8	S6R1608V1M	3.3	10	48TSOP1	Now
					54TSOP2	U/C
		S6R1608C1M	5.0	10	48TSOP1	Now
					54TSOP2	U/C

■ Wafer Product

Density	Org.	Part Number	Vdd (V)	Speed -tAA(ns)	Test Level	Availability
1Mb~16Mb	x32/16/8/4	S6R16-1M	3.3/5	10	W1	Now

Notes

1. All of packaged asynchronous fast products are based on RoHS6 or lead free.
2. Industrial temperature range is recommended, but commercial one is available.
3. U/C, under consideration, stands for products available upon request.

High Quality & High Performance Memory Provider for Network Solution

Synchronous SRAM Code Information (1/2)

Standard Sync., Quadruple & DDR

S 7 X X X X X X X X - X X X X X X X X
 1 2 3 4 5 6 7 8 9 10 11 12 13 14 15 16 17 18

(1) Netsol Memory : S

(2) Sync SRAM : 7

(3) Functional Mode

- A : Sync Pipelined Burst
- B : Flow Through
- H : Double Data Rate I, Common I/O
- I : Double Data Rate II, Common I/O
- J : Double Data Rate II, Separate I/O
- K : Double Data Rate II+, Common I/O
- L : Double Data Rate II+, Common I/O with ODT
- M : NTSRAM + Flow Through
- N : NTSRAM + Sync Pipelined Burst
- Q : Quadruple SRAM I
- R : Quadruple SRAM II
- S : Quadruple SRAM II+
- T : Quadruple SRAM II+ with ODT

(4) ~ (5) Density

- | | |
|--------------|--------------|
| 40 : 4M~4.5M | 80 : 8M~9M |
| 16 : 16M~18M | 32 : 32M~36M |
| 64 : 64M~72M | 44 : 144M |
| 28 : 288M | 57 : 576M |
| 1G : 1G | |

(6) ~ (7) Organization

- | | |
|-----------|----------|
| 08 : x8 | 09 : x9 |
| 18 : x18 | 32 : x32 |
| 36 : x36 | 72 : x72 |
| 44 : x144 | |

(8) ~ (9) Vcc, Interface, Mode

- 30 : 2.5V/3.3V Wide, LVTTTL, 2E1D
- 31 : 2.5V/3.3V Wide, LVTTTL, 2E2D
- 35 : 2.5V/3.3V Wide, LVTTTL, SB-FT
- 62 : 2.5V/1.8V, HSTL, Burst2
- 64 : 2.5V/1.8V, HSTL, Burst4
- 82 : 1.8V, HSTL, Burst2
- 84 : 1.8V, HSTL, Burst4
- T2 : 1.8V, 2clock latency, Burst2
- T4 : 1.8V, 2clock latency, Burst4
- U2 : 1.8V, 2.5clock latency, Burst2
- U4 : 1.8V, 2.5clock latency, Burst4

(10) Generation

- | | |
|--------------------|--------------------|
| M : 1st Generation | A : 2nd Generation |
| B : 3rd Generation | C : 4th Generation |

(11) “—”

Synchronous SRAM Code Information (2/2)

Standard Sync., Quadruple & DDR

S 7 X X X X X X X X - X X X X X X X X
 1 2 3 4 5 6 7 8 9 10 11 12 13 14 15 16 17 18

(12) Package

- P : TQFP(LF)
- Q : TQFP
- E : FBGA(LF)
- F : FBGA
- G : PBGA(LF)
- H : PBGA
- LF means Lead Free

(13) Temp

- A : Automotive (-40°C ~ +125°C)
- I : Industrial (-40°C ~ +85°C)
- C : Commercial (0°C ~ +70°C)

(14)~(15) Speed

- SPB, NT-SPB, DDR,
- DDR- I/ II/ II+, Quadruple- I/ II/ II+
- 13 : 133MHz 16 : 166MHz
- 20 : 200MHz 25 : 250MHz
- 30 : 300MHz 33 : 333MHz
- 40 : 400MHz 45 : 450MHz
- 50 : 500MHz 55 : 550MHz
- 60 : 600MHz 65 : 650MHz
- 66 : 666MHz 70 : 700MHz
- 75 : 750MHz

● FT, NT-FT

- 60 : 6.0ns 65 : 6.5ns
- 70 : 7.0ns 75 : 7.5ns
- 80 : 8.0ns 85 : 8.5ns
- 90 : 9.0ns 10 : 10ns

(16) Packing "Packing Type Reference"

Marking	Packing Type
0 (Number)	Tray, Tube
T	Tape & Reel

(17)~(18) Special code for customer demand

00 : default

* Note

(1) ~ (14) : customer ordering code,
 appears on top of PKG

(16) ~ (18) : code for Labeling,
 appears on label on Box

Asynchronous Fast SRAM

Packaged Product Code Information



(1) Netsol Memory : S

(2) Async SRAM : 6

(3) Functional Mode

R : Fast SRAM

(4) ~ (5) Density

40 : 4M

80 : 8M

16 : 16M

32 : 32M

64 : 64M

(6) ~ (7) Organization

04: x4

08 : x8

16 : x16

(8) Vcc

C : 5.0V

V : 3.3V

U : 3.0V

S : 2.5V

(9) Mode

1 : CS Low Active

2 : CS1, CS2 - Chip Select Signal

3 : CS1, CS2, CS3 - Chip Select Signal

(10) Generation

M : 1st Generation

A : 2nd Generation

B : 3rd Generation

C : 4th Generation

(11) “—”

(12) Package

U : 44TSOP2(LF)

S : 54TSOP2(LF)

Y : 48TSOP1(LF)

(13) Temp

A : Automotive (-40°C ~ +125°C)

I : Industrial (-40°C ~ +85°C)

C : Commercial (0°C ~ +70°C)

(14)~(15) Speed (tAA)

08 : 8ns

09 : 9ns

10 : 10ns

12 : 12ns

(16) Packing “Packing Type Reference”

Marking	Packing Type
0 (Number)	Tray, Tube
T	Tape & Reel

(17)~(18) Special code for customer demand

00 : default

* Note

(1) ~ (14) : customer ordering code, appears on top of PKG

(16) ~ (18) : code for Labeling, appears on label on Box

High Quality & High Performance Memory Provider for Network Solution



Asynchronous Fast SRAM

Wafer/Chip Code Information

S 6 X X X - X X - X X X X X X X
 1 2 3 4 5 6 7 8 9 10 11 12 13 14 15 16

(1) Netsol Memory : S

(2) Async SRAM : 6

(3) Functional Mode

R : Fast SRAM

(4) ~ (5) Density

40 : 4M	80 : 8M
16 : 16M	32 : 32M
64 : 64M	

(6) “—”

(7) Mode

1 : CS Low Active
 2 : CS1, CS2 - Chip Select Signal
 3 : CS1, CS2, CS3 - Chip Select Signal

(8) Generation

M : 1st Generation	A : 2nd Generation
B : 3rd Generation	C : 4th Generation

(9) “—”

(10) Product form

W : Wafer
 C : Chip

(11) Test Level

1 : Hot Temp, DC sort
 2 : Hot Temp, DC and selected AC sort
 3 : Ho and Cold Temp,
 DC and selected AC sort

(12) Carrier Type

0 : Cassette type
 1 : Jar type

(13)~(16) Special code for customer demand

0000 : default

*** Note**

(1) ~ (11) : customer ordering code

(12) ~ (16) : code for Labeling, appears on label on Box